IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Original): A semiconductor device comprising:

a heat sink comprising a bottom surface exposed to the outside and an upper surface opposed to said bottom surface;

an insulating substrate jointed to said upper surface of said heat sink;

a conductive plate jointed to an upper surface of said insulating substrate;

a first semiconductor chip comprising a first main electrode electrically connected through a first conductive layer to an upper surface of said conductive plate, and a second main electrode opposed to and having a smaller area than said first main electrode;

a second semiconductor chip comprising a first main electrode electrically connected through a second conductive layer to and having a smaller area than said second main electrode of said first semiconductor chip, and a second main electrode opposed to said first main electrode; and

a container enclosing said heat sink except an exposed portion of said bottom surface, said insulating substrate, said conductive plate, said first semiconductor chip and said second semiconductor chip in its interior space,

wherein a portion above said second main electrode of said second semiconductor chip is said interior space of said container, and

wherein a base material of said second semiconductor chip is a wide gap semiconductor having a greater interband energy gap than silicon.

Claim 2 (Original):. The semiconductor device according to claim 1, wherein

a base material of said first semiconductor chip is also said wide gap semiconductor.

Claim 3 (Original): The semiconductor device according to claim 1, wherein

said first semiconductor chip is located on a first region of said upper surface of said conductive plate with said first conductive layer sandwiched in between,

said semiconductor device further comprising:

another first semiconductor chip comprising a first main electrode electrically connected through another first conductive layer to a second region of said upper surface of said conductive plate, and a second main electrode opposed to and having a smaller area than said first main electrode; and

another second semiconductor chip comprising a first main electrode electrically connected through another second conductive layer to and having a smaller area than said second main electrode of said another first semiconductor chip, and a second main electrode opposed to said first main electrode,

wherein said container also encloses said another first semiconductor chip and said another second semiconductor chip in said interior space, and

wherein a base material of said another second semiconductor chip is said wide gap semiconductor.

Claim 4 (Original): A semiconductor device comprising:

a heat sink comprising a bottom surface exposed to the outside and an upper surface opposed to said bottom surface;

an insulating substrate jointed to said upper surface of said heat sink;

a conductive plate jointed to an upper surface of said insulating substrate;

a first semiconductor chip comprising a first main electrode electrically connected through a first conductive layer to a first surface portion of an upper surface of said conductive plate, and a second main electrode opposed to said first main electrode with

respect to a first direction which is equivalent to a direction of a normal to said upper surface of said conductive plate;

a metal base having a first portion and a second portion,

said first portion having a first end which is electrically connected through a second conductive layer to a second surface portion of said upper surface of said conductive plate adjacent to said first surface portion, and extending from said first end to a second end in said first direction,

said second portion being coupled to said second end of said first portion and extending in a second direction orthogonal to said first direction so as to form an L-shape with said first portion;

a second semiconductor chip comprising a first main electrode electrically connected through a third conductive layer to an upper surface of said second portion of said metal base, and a second main electrode opposed to said first main electrode with respect to said first direction; and

a container enclosing said heat sink except an exposed portion of said bottom surface, said insulating substrate, said conductive plate, said first semiconductor chip, said metal base and said second semiconductor chip in its interior space,

wherein a lower surface of said second portion of said metal base is above the level of an upper surface of said second main electrode of said first semiconductor chip, and

wherein a base material of said second semiconductor chip is a wide gap semiconductor having a greater interband energy gap than silicon.

Claim 5 (Original): The semiconductor device according to claim 4, wherein a base material of said first semiconductor chip is also said wide gap semiconductor.

Claim 6 (Original): The semiconductor device according to claim 4, further comprising:

another first semiconductor chip comprising a first main electrode electrically connected through another first conductive layer to a third surface portion of said upper surface of said conductive plate, and a second main electrode opposed to said first main electrode with respect to said first direction;

another metal base having a first portion and a second portion,

said first portion of said another metal base having a first end which is electrically connected through another second conductive layer to a fourth surface portion of said upper surface of said conductive plate adjacent to said third surface portion, and extending from said first end to a second end in said first direction,

said second portion of said another metal base being coupled to said second end of said first portion of said another metal base and extending in said second direction to form an L-shape with said first portion; and

another second semiconductor chip comprising a first main electrode electrically connected through another third conductive layer to an upper surface of said second portion of said another metal base, and a second main electrode opposed to said first main electrode with respect to said first direction,

wherein said container also encloses said another first semiconductor chip, said another base metal and said another second semiconductor chip in said interior space,

wherein a lower surface of said second portion of said another metal base is above the level of an upper surface of said second main electrode of said another first semiconductor chip, and

wherein a base material of said another second semiconductor chip is said wide gap semiconductor.

Claims 7-10 (Canceled).